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DISCRETE POWER & SIGNAL TECHNOLOGIES

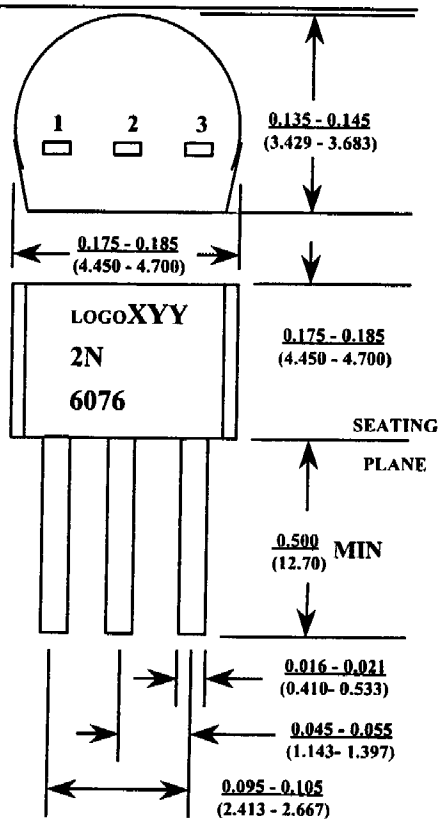
2N6076

SILICON PNP SMALL SIGNAL TRANSISTOR

BVCEO . . . . 25 V (Min)

hFE . . . . 100 (Min) @ VCE = 10 V, IC = 10 mA

1	2	3
B	C	E



ABSOLUTE MAXIMUM RATINGS (NOTE 1)

TEMPERATURES

Storage Temperature	-55 Degrees C to 150 Degrees C
Operating Junction Temperature	150 Degrees C

POWER DISSIPATION (NOTES 2 & 3)

Total Device Dissipation at TA = 25 Deg C	625 mW

VOLTAGES & CURRENT

VCEO	Collector to Emitter	25 V
VCBO	Collector to Base	25 V
VEBO	Emitter to Base	5 V
IC	Collector Current	500 mA

ELECTRICAL CHARACTERISTICS (25 Degrees C Ambient Temperature unless otherwise stated)

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
BVCBO	Collector to Base Voltage	25		V	IC = 100 uA
BVCEO	Collector to Emitter Voltage	25		V	IC = 10 mA
BVEBO	Emitter to Base Voltage	5		V	IE = 10 uA
ICBO	Collector Cutoff Current		100	nA	VCB = 25 V
			10	uA	VCB = 25 V, T=+100°C
ICES	Collector Cutoff Current		100	nA	VCE = 25 V
IEBO	Emitter Cutoff Current		100	uA	VEB = 3.0 V
hFE	DC Current Gain	100	500		VCE = 10 V IC = 10 mA
VCE(sat)	Collector-Emitter Saturation Voltage		0.25	V	IC = 10mA IB = 1.0mA
VBE(sat)	Base-Emitter Saturation Voltage		0.8	V	IC = 10mA IB = 1.0mA
VBE(on)	Base -Emitter On Voltage	0.5	1.2	V	VCE = 10 V IC = 10mA